

IN THE CLAIMS

Please add new claims 36-44 as shown in the following detailed claim listing. No claims are amended by way of this Preliminary Amendment.

1. (Original) An integrated circuit fabricated by:
forming a first dielectric layer in a manner that varies in the Z-dimension; and
forming a first conductive layer over the first dielectric layer, the first conductive layer also varying in the Z-dimension, the first conductive layer having a length and a width, the length being substantially greater than the width, the first conductive layer being arranged in a substantially straight line along the X-dimension, and the first conductive layer comprising upper segments and lower segments, the upper segments being longer than the lower segments.
2. (Original) The integrated circuit recited in claim 1 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in a stepped manner.
3. (Original) The integrated circuit recited in claim 1 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in an undulating manner.
4. (Original) The integrated circuit recited in claim 1 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in a manner that alternates between trenches and pedestals.
5. (Original) An integrated circuit as recited in claim 1 and further fabricated by:
forming a second dielectric layer in a manner that varies in the Z-dimension;
forming a second conductive layer over the second dielectric layer, the second conductive layer also varying in the Z-dimension, the second conductive layer having a length and a width, the length being substantially greater than the width, the second conductive layer being arranged in a substantially straight line along the X-dimension, and the second conductive layer comprising upper segments and lower segments, the upper segments being longer than the lower segments; and

coupling the second conductive layer to the first conductive layer.

6. (Original) The integrated circuit recited in claim 5 wherein, in forming the second conductive layer, the upper segments in the first conductive layer are offset 180 degrees from the upper segments in the second conductive layer.

7. (Original) The integrated circuit recited in claim 1 wherein, in forming the first conductive layer, the first conductive layer comprises material from the group consisting of copper, aluminum, tungsten, molybdenum, titanium, gold, silver, palladium, a metal silicide, doped polysilicon, or is an alloy whose constituents are from the group.

8. (Original) The integrated circuit recited in claim 1 wherein, in forming the first conductive layer, the first conductive layer comprises magnetic material.

9. (Original) The integrated circuit recited in claim 8 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of nickel-iron, cobalt-zirconium-tantalum, iron-tantalum-nickel, nickel-iron-rhenium, and ferro-silicon.

10. (Original) The integrated circuit recited in claim 8 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of iron, nickel, cobalt, manganese, zinc, zirconium, tantalum, rhenium, silicon, and the rare earth elements, or is an alloy whose constituents are from the group.

11-35. (Canceled)

36. (New) An integrated circuit fabricated by:
- forming a first dielectric layer that varies in the Z-dimension;
 - forming a first conductive layer over the first dielectric layer, the first conductive layer also varying in the Z-dimension, the first conductive layer having a length and a width, the length being substantially greater than the width, the first conductive layer being arranged in a substantially straight line along the X-dimension, and the first conductive layer comprising upper segments and lower segments, the upper segments being longer than the lower segments.
 - forming a second dielectric layer that varies in the Z-dimension;
 - forming a second conductive layer over the second dielectric layer, the second conductive layer also varying in the Z-dimension, the second conductive layer having a length and a width, the length being substantially greater than the width, the second conductive layer being arranged in a substantially straight line along the X-dimension, and the second conductive layer comprising upper segments and lower segments, the upper segments being longer than the lower segments; and
 - coupling the second conductive layer to the first conductive layer.
37. (New) The integrated circuit recited in claim 36 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in a stepped manner.
38. (New) The integrated circuit recited in claim 36 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in an undulating manner.
39. (New) The integrated circuit recited in claim 36 wherein, in forming the first dielectric layer, the first dielectric layer is arranged in a manner that alternates between trenches and pedestals.
40. (New) The integrated circuit recited in claim 36 wherein, in forming the second conductive layer, the upper segments in the first conductive layer are offset 180 degrees from the upper segments in the second conductive layer.

41. (New) The integrated circuit recited in claim 36 wherein, in forming the first conductive layer, the first conductive layer comprises material from the group consisting of copper, aluminum, tungsten, molybdenum, titanium, gold, silver, palladium, a metal silicide, doped polysilicon, or is an alloy whose constituents are from the group.

42. (New) The integrated circuit recited in claim 36 wherein, in forming the first conductive layer, the first conductive layer comprises magnetic material.

43. (New) The integrated circuit recited in claim 42 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of nickel-iron, cobalt-zirconium-tantalum, iron-tantalum-nickel, nickel-iron-rhenium, and ferro-silicon.

44. (New) The integrated circuit recited in claim 42 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of iron, nickel, cobalt, manganese, zinc, zirconium, tantalum, rhenium, silicon, and the rare earth elements, or is an alloy whose constituents are from the group.

45. (New) An integrated circuit fabricated by:

forming a first dielectric layer that varies in the Z-dimension;

forming a first conductive layer over the first dielectric layer, the first conductive layer also varying in the Z-dimension, the first conductive layer having a length and a width, the length being substantially greater than the width, the first conductive layer being arranged in a substantially straight line along the X-dimension, and the first conductive layer comprising upper segments and lower segments, the upper segments being longer than the lower segments,

wherein, in forming the first conductive layer, the first conductive layer comprises magnetic material.

RESPONSE TO RESTRICTION REQUIREMENT

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46. (New) The integrated circuit recited in claim 45 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of nickel-iron, cobalt-zirconium-tantalum, iron-tantalum-nickel, nickel-iron-rhenium, and ferro-silicon.

47. (New) The integrated circuit recited in claim 45 wherein, in forming the first conductive layer, the magnetic material is from the group consisting of iron, nickel, cobalt, manganese, zinc, zirconium, tantalum, rhenium, silicon, and the rare earth elements, or is an alloy whose constituents are from the group.